SHEET 1 OF 2 SERIAL NO. ORMATION DISCLOSURE ATTY. DOCKET NO. 10/756,829 055071-0328 CITATION IN AN APPLICATION **APPLICANT** Robert John SOCHA, et al. FILING DATE GROUP (PTO-1449) 2825 January 14, 2004 **U.S. PATENT DOCUMENTS** Document Number Publication Date Name of Patentee or Applicant of Cited Pages, Columns, Lines, Where **EXAMINER'S** CITE MM-DD-YYYY Document Relevant Passages or Relevant INITIALS NO. Number-Kind Code2 (# known Figures Appear 6,413,684 B1 07/02/2002 Stanton 7S.M./ US 6,355,382 B1 03/12/2002 Yasuzato et al. 5,229,230 07/20/1993 Kamon US US 5,895,741 04-20-1999 Hasegawa et al. US 6,214,497 B1 04-10-2001 Stanton 2002/0152452 A1 10-17-2002 Socha US US 5,682,323 10-28-1997 Pasch et al. US 6,303,253 B1 10-16-2001 Wong et al. US 6.223.139 B1 04-24-2001 Pierrat, Christophe US 6,777,141 08-2004 Cote et al. ·US 6,787,271 09-2004 US 2002/0083410 06-2002 Wu et al. 09-2004 Shi et al. ÜS 6,792,591 02-2003 Shi et al. US 6,519,760 2003/0228541 12-2003 Hau et al. US 2002/0157081 ShI et al. US 10-2002 υŝ 6.807.662 10-2004 Toublan et al. US 2004/0122636 06-2004 Adam, Konstantinos FOREIGN PATENT DOCUMENTS Foreign Patent Document Pages, Columns, Lines Translation **Publication Date** Name of Patentee or **FXAMINER'S** Applicant of Cited Document Where Relevant INITIALS Country Codes-Number 4-Kind Codes (if known) MM-DD-YYYY CITE Yes No Figures Appear OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, **EXAMINER'S** INITIALS journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where CITE published.

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<u>/Suresh Memula/</u>

SHEET 2 OF 2 ATTY, DOCKET NO. SERIAL NO. ORMATION DISCLOSURE 055071-0328 10/756,829 CITATION IN AN **APPLICATION APPLICANT** Robert John SOCHA, et al. FILING DATE **GROUP** (PTO-1449) January 14, 2004 2825 **U.S. PATENT DOCUMENTS** EXAMINER'S INITIALS CITE NO. Document Number **Publication Date** Name of Patentee or Applicant of Cited Pages, Columns, Lines, Where MM-DD-YYYY Document Relevant Passages or Relevant Number-Kind Codes (# known Figures Appear US FOREIGN PATENT DOCUMENTS **EXAMINER'S** Foreign Patent Document **Publication Date** Name of Patentee or Pages, Columns, Lines Translation **Applicant of Cited Document** INITIALS Where Relevant Country Codes -Number 4 -Kind Codes (if known) CITE MM-DD-YYYY Yes Figures Appear NUMERICAL 01/10/2002 WO 02/03140 A1 TECHNOLOGIES, INC. /S.M./ ASML MASKTOOLS B.V. 09/04/2002 EP 1 237 046 A2 × 05-02-2002 ASML Masktools B.V. EP 1 202 119 A1 WO 03/054826 A1 07-03-2003 ADVANCED MICRO /S.M./ DEVICES, INC.

		OTHER ART (Including Auti	hor, Title, Date, Pertinent Pages, Etc.)				
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTEF journal, serial, symposium, catalog, etc.), date, p published.	lude name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, rnal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where blished.				
/S.M./		Christoph DOLAINSKY, et al., "Simulation based method for sidelobe suppression," Optical Microlithography XIII Proceedings of SPIE, 2000, pp 1156-1162, Vol. 4000					
			generation to consol unexposted images at sidelabe everlap regions in attenuated phase-shift masks,"				
/S.M./		Nicolas Bailey COBB, "Fast Optical and Process Proximity Correction Algorithms for Integrated Circuit Manufacturing," Ph.D. dissertation, Spring 1998, pp 35-72, University of California at Berkeley					
		J. Fung CREN, et al., Practicari-Eine OPC Contact wasks for Sub-0.3Miltron Design Kuie Application: Part 1—OPC Design Optimization," pp 181-201					
/S.M./		J.A. TORRES, et al., "Contrast-Based Assist Feature Optimization," Optical Microlithography XV, 2002, pp 179-187, Proceedings of SPIE, Vol 4691, SPIE					
/S.M./	 	Olivier TOUBLAN, et al., "Fully Automatic Side Lobe Detection and Correction Technique for Attenuated Phase Shift Masks," Optical Microlithography XIV, 2001, pp 1541-1547, Proccedings of SPIE, Vol. 4346, SPIE					
/S.M./		Michael S. YEUNG, "Extension of the Hopkins theory of partially coherent imaging to include thin-film interference effects," Optical/Laser Microlithography VI, 1993, pp 452-463, SPIE, Vol. 1927					
/S.M./		Douglas VAN DEN BROEKE, et al., "Near 0.3 k, Full Pitch Range Contact Hole Patterning Using Chromeless Phase Lithography (CPL)," Proceedings of the SPIE, September 9, 2003, pp 297-308, Vol. 5256, SPIE					
EXAMINER			DATE CONSIDERED				

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered.

08/28/2007

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U.S. PATENT DOCUMENTS										
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EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the stricte (when appropriate), little of the Item (book, magazine, journel, serial, sympostum, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.								
/S.M./		Kyoji NAKAJO, et al., "Auxillary pattern generation to cancel unexpected images at sidelobe overlap regions in attenuated phase-shift masks," SPIE VOL. 3748, September 1999, pp. 214-221.								
/S.M./		J. Fung CHEN, et al., "Practical I-Line OPC Contact Masks for Sub-0.3Micron Design Rule Application: Part 1—OPC Design Optimization," pp 181-201, 1997								
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EXAMINER				DATE CONSIDERED						
/Suresh Memula/			08/28/2007							

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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